

**IN THE CLAIMS**

Please substitute claims 1-32 with the following:

1. (Canceled).

2. (Previously Presented) A semiconductor light emitting device comprising:

a supporting base;

a first semiconductor light emitting element comprising a first substrate and an electrode, wherein the first semiconductor light emitting element is provided on one face of the supporting base and the electrode is electrically connected to the first substrate; and

a second semiconductor light emitting element stacked on the first light emitting element, the second semiconductor light emitting element provided on a side of the first light emitting element facing away from the supporting base, wherein:

the second semiconductor light emitting element comprises a second substrate, a first lasing portion and a second lasing portion;

the first lasing portion includes a first lasing electrode electrically isolated from the first substrate; and

the second lasing portion includes a second lasing electrode electrically connected to the electrode.

3. (Original) A light emitting device according to claim 2, wherein the first substrate is transparent in the visible region.

4. (Original) A light emitting device according to claim 2, wherein the first and second light emitting elements can emit light of different wavelengths.

5. (Original) A light emitting device according to claim 2, wherein the first light emitting element has a semiconductor layer containing at least one of Group 3B elements and at least nitrogen (N) from Group 5B elements.

6. (Original) A light emitting device according to claim 5, wherein the first substrate is made of either a Group III-V compound semiconductor of the nitride system containing at least one of Group 3B elements and at least nitrogen (N) from Group 5B elements, or sapphire ( $\text{Al}_2\text{O}_3$ ).

7. (Original) A light emitting device according to claim 2, wherein the first light emitting element has a light emitting portion on the first substrate on the side thereof on which the supporting base is disposed.

8. (Original) A light emitting device according to claim 2, wherein the second light emitting element has a light emitting portion on the second substrate on the side thereof on which the first light emitting element is disposed.

9. (Original) A light emitting device according to claim 2, wherein the second light emitting element has a plurality of light emitting portions of different output wavelengths.

10. (Original) A light emitting device according to claim 2, wherein the second substrate is made of gallium arsenide (GaAs).

11. (Original) A light emitting device according to claim 2, wherein the second light emitting element has a semiconductor layer containing at least gallium (Ga) from Group 3B elements and at least arsenide (As) from Group 5B elements.

12. (Original) A light emitting device according to claim 2, wherein the second light emitting element has a semiconductor layer containing at least indium (In) from Group 3B elements and phosphorus (P) from Group 5B elements.

13. (Original) A light emitting device according to claim 2, wherein the second light emitting element has a semiconductor layer containing at least one element selected from the group of Group 2A or 2B elements consisting of zinc (Zn), cadmium (Cd), mercury (Hg), beryllium (Be) and magnesium (Mg), and at least one element selected from the group of Group 6B elements consisting of sulfur (S), selenium (Se) and tellurium (Te).

14. (Previously Presented) A semiconductor light emitting device as set forth in claim 2 wherein each of said first and second semiconductor light emitting elements emits a light beam in a direction that is perpendicular to a direction in which said first and second semiconductor light emitting elements is stacked.

15. (Cancelled).

16. (Previously Presented) A semiconductor light emitting device comprising:

a supporting base;

a first light emitting element provided on one face of the supporting base and comprising a first substrate and an electrode, wherein the first substrate is provided on a side of said first light emitting element facing away from said supporting base and the electrode is electrically connected to the first substrate;

a second light emitting element stacked on the first light emitting element, wherein the second light emitting element comprises a second substrate, a first lasing portion and a second

lasing portion, wherein the second substrate is provided on a side of the second light emitting element facing away from the supporting base; and wherein:

the first lasing portion includes a first lasing electrode electrically isolated from the first substrate;

the second lasing portion includes a second lasing electrode electrically connected to the electrode; and

the first substrate is transparent in the visible region.

17. (Previously Presented) The semiconductor light emitting device of claim 2, wherein said first substrate is provided on a side of said first light emitting element opposite said supporting base.

18. (Previously Presented) An optical device including a semiconductor light emitting device, the semiconductor light emitting device comprising:

a supporting base;

a first light emitting element comprising a first substrate and an electrode, wherein the first semiconductor light is provided on one face of the supporting base and the electrode is electrically connected to the first substrate; and

a second light emitting element stacked on the first light emitting element, the second light emitting element comprising a second substrate, a first lasing portion and a second lasing portion, wherein:

the second substrate is provided on a side of the second light emitting element opposite to the supporting base;

the first lasing portion includes a first lasing electrode electrically isolated from the first substrate; and

the second lasing portion includes a second lasing electrode electrically connected to the electrode.

19. (Previously Presented) The optical device of claim 18, wherein the first and second light emitting elements can emit light of different wavelengths.

20. (Previously Presented) The optical device of claim 18, wherein the first light emitting element has a semiconductor layer containing at least one of Group 3B elements and at least nitrogen (N) from Group 5B elements.

21. (Previously Presented) The optical device of claim 18, wherein the first substrate is made of either a Group III-V compound semiconductor of the nitride system containing at least one of Group 3B elements and at least nitrogen (N) from Group 5B elements, or sapphire ( $\text{Al}_2\text{O}_3$ ).

22. (Previously Presented) The optical device of claim 18, wherein the first light emitting element has a light emitting portion on the first substrate on the side thereof on which the supporting base is disposed.

23. (Previously Presented) The optical device of claim 18, wherein the second light emitting element has a light emitting portion on the second substrate on the side thereof on which the first light emitting element is disposed.

24. (Previously Presented) The optical device of claim 18, wherein the second light emitting element has a plurality of light emitting portions of different output wavelengths.

25. (Previously Presented) The optical device of claim 18 wherein the second substrate is made of gallium arsenide (GaAs).

26. (Previously Presented) The optical device of claim 18, wherein the second light emitting element has a semiconductor layer containing at least gallium (Ga) from Group 3B elements and at least arsenide (As) from Group 5B elements.

27. (Previously Presented) The optical device of claim 18, wherein the second light emitting element has a semiconductor layer containing at least indium (In) from Group 3B elements and phosphorus (P) from Group 5B elements.

28. (Previously Presented) The optical device of claim 18, wherein the second light emitting element has a semiconductor layer containing at least one element selected from the group of Group 2A or 2B elements consisting of zinc (Zn), cadmium (Cd), mercury (Hg), beryllium (Be) and magnesium (Mg), and at least one element selected from the group of Group 6B elements consisting of sulfur (S), selenium (Se) and tellurium (Te).

29. (Previously Presented) The optical device of claim 18, wherein said first substrate is provided on a side of said first light emitting element opposite said supporting base.

30. (Previously Presented) An optical device as set forth in claim 18, wherein the first substrate is transparent in the visible region.

31. (Previously Presented) An optical device as set forth in claim 18, wherein each of said first and second semiconductor light emitting elements emits a light beam in a direction that is perpendicular to a direction in which said first and second semiconductor light emitting elements is stacked.

32. (Previously Presented) The semiconductor light emitting device as set forth in claim 16, wherein each of said first and second semiconductor light emitting elements emits a light beam in a direction that is perpendicular to a direction in which said first and second semiconductor light emitting elements is stacked.

33. (Previously Presented) A semiconductor light emitting device as set forth in claim 16, wherein each of said first and second semiconductor light emitting elements emits a light beam in a direction that is perpendicular to a direction in which said first and second semiconductor light emitting elements is stacked.